# SEMIKRON INC

#### **Maximum Ratings**

Symbol	Conditions	Values	Units
VCEVsus	I <sub>C</sub> = 1 A, V <sub>BE</sub> = -2 V	1000	V
Vcev	V <sub>BE</sub> = -2 V	1000	V
V <sub>CBO</sub>	l∈ = 0	1000	V
V <sub>EBO</sub>	Ic = 0	7	V
lc	D. C.	50	Α
Ісм	t <sub>p</sub> = 1 ms	100	Α
lf = -lc	D. C.	50	Α
lв		3	Α
P <sub>tot</sub>	T <sub>case</sub> = 25 °C, per darlington	400	W
Tvj		- 40 · · · + 150	°C
T <sub>stg</sub>		- 40 + 125	°C
Visol	a. c. 50 Hz, r.m.s.	2500~	٧

#### **Thermal Characteristics**

Rthjc	per darlington/per module	0,31/0,15	°C/W
Rthjc	per diode/per module	1,2/0,6	°C/W
Rthch	per ½ module/per module	0,15/0,075	°C/W

## Electrical Characteristics<sup>1)</sup>

	"		min.	typ.	max.	
ICEV	$V_{CE} = V_{CEV}$ , $V_{BE} = -2 V$				1	mΑ
IEBO	$I_C = 0$ , $V_{BE} = -7 \text{ V}$	72.7			200	mΑ
V <sub>CEsat</sub> <sup>2)</sup>	Ic = 50 A, I <sub>B</sub> = 1 A				2,5	٧
V <sub>BEsat</sub> <sup>2)</sup>	Ic = 50 A, I <sub>B</sub> = 1 A				3,5	٧
h <sub>21E</sub> <sup>2)</sup>	I <sub>C</sub> = 50 A	$V_{CE} = 2,8 \text{ V}$	75			
11216	10 - 50 A	$V_{CE} = 5 \text{ V}$	100			

Switching Characteristics for Resistive Load<sup>1)</sup>

	ton	) Ic = 50 A	0,8	2,5	μs
į	ts	} I <sub>B1</sub> = − I <sub>B2</sub> = 1 A	11	15	μs
	tr	Vcc = 600 V	2	3	μs

### Inverse Diode Characteristics1)

	de endracteriones				
V <sub>F</sub> = -V <sub>CE</sub>	I <sub>F</sub> = - I <sub>C</sub> = 50 A			1,75	٧
I <sub>FSM</sub> = - I <sub>Cp</sub>	sin 180°, 10 ms	500			Α
I <sub>RM</sub>	$ \begin{cases} I_F = -I_C = 50 \text{ A, } - \text{dir/dt} = 100 \text{ A/} \mu \text{s} \\ V_{BE} = -3 \text{ V, } V_R = V_{CE} = 400 \text{ V,} \end{cases} $		35		Α
Q <sub>rr</sub>	T <sub>vj</sub> = 125 °C		17		μC

# Mechanical Data

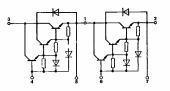
M <sub>1</sub>	Case to heatsink	SI units	3		6	Nm
1411	Case to Heatsilik	US units	27		53	lb. in.
M <sub>2</sub>	Busbars to terminals	SI units	2,5		5	Nm
IVI2	Duspais to terminais	US units	22		44	lb. in.
W				250		g
Case		DB		D 11		
Case		DAL		D 21		

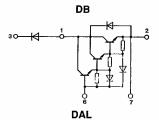
 $^{1)}$   $T_{case}$  = 25 °C unless otherwise stated  $^{2)}$   $t_{p} \leq~300~\mu s,~D~\leq~1,5~\%$ 

**SEMITRANS® 2** NPN **Power Darlington Modules** 50 A, 1000 V 7-33-35

SK 50 DB 100 D SK 50 DAL 100 D







#### **Features**

- Isolated baseplate (ease of mounting of one or several modules on one heatsink)
- All electrical connections on top (ease of interconnecting of modules with busbars/PCB)
- Large clearances and creepage distances
- Parallel connected fast recovery inverse diode

  UL recognized, file no. 63 532

## **Typical Applications**

- Switched mode power supplies DC servo and robot drives AC motor controls Brake choppers (DAL)

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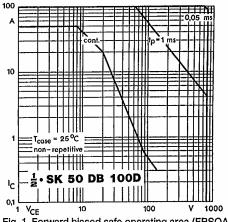


Fig. 1 Forward biased safe operating area (FBSOA)

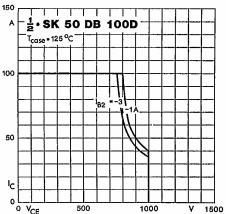


Fig. 3 Reverse biased safe operating area (RBSOA)

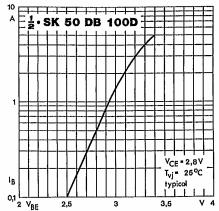


Fig. 5 Base current/voltage characteristic

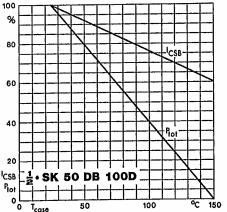


Fig. 2 Shifting the limits of the FBSOA with temperature

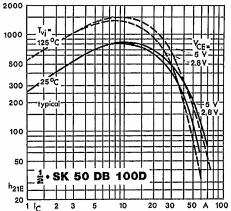


Fig. 4 Forward current transfer ratio vs. coll. current

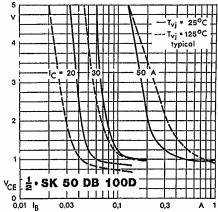


Fig. 6 Collector-emitter voltage vs. base current

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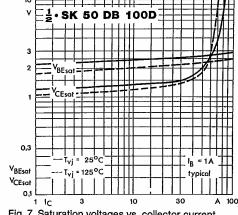


Fig. 7 Saturation voltages vs. collector current

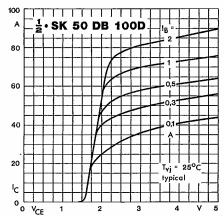


Fig. 9 Collector current/voltage characteristics

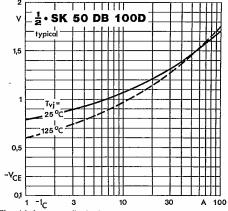


Fig. 11 Inverse diode forward characteristics

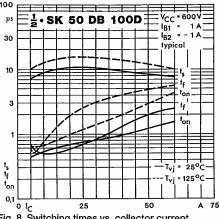


Fig. 8 Switching times vs. collector current

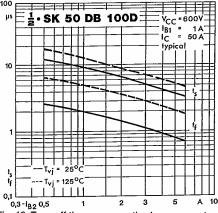


Fig. 10 Turn-off times vs. negative base current

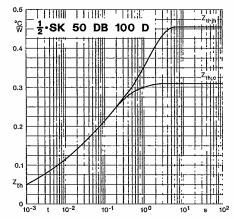
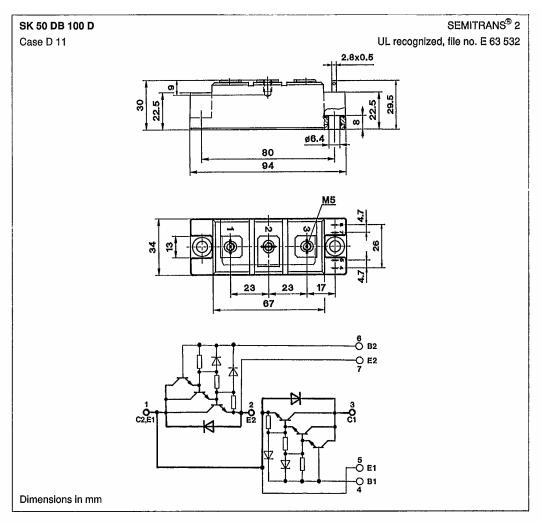
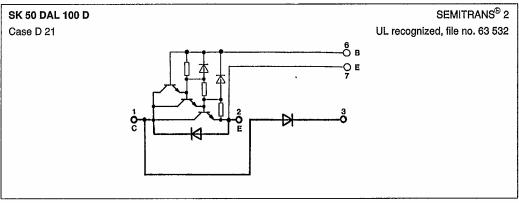


Fig. 12 Transient thermal impedance vs. time

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